



**THE DATASHEET OF
NSV40200UW6T1G**



40 V, 2.0 A, Low $V_{CE(sat)}$ PNP Transistor

NSS40200UW6T1G, NSV40200UW6T1G

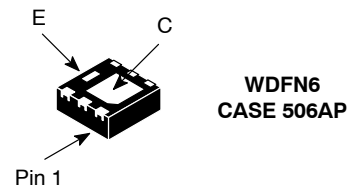
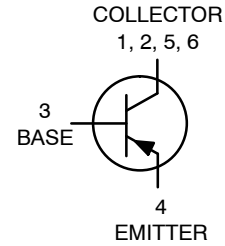
onsemi's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

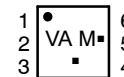
Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

-40 VOLTS
2.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 100 m Ω



MARKING DIAGRAM



VA = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS40200UW6T1G	WDFN6 (Pb-Free)	3000/ Tape & Reel
NSV40200UW6T1G	WDFN6 (Pb-Free)	3000/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSS40200UW6T1G, NSV40200UW6T1G

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-40	Vdc
Collector-Base Voltage	V_{CBO}	-40	Vdc
Emitter-Base Voltage	V_{EBO}	-7.0	Vdc
Collector Current - Continuous	I_C	-2.0	Adc
Collector Current - Peak	I_{CM}	-4.0	A
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	875 7.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	143	$^\circ\text{C}/\text{W}$
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	1.5 11.8	W mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	85	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Lead #1	$R_{\theta JL}$ (Note 2)	23	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 sec)	$P_{D\text{single}}$ (Notes 2 & 3)	3.0	W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ 100 mm², 1 oz copper traces.
2. FR-4 @ 500 mm², 1 oz copper traces.
3. Thermal response.

NSS40200UW6T1G, NSV40200UW6T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typical	Max	Unit
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OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage ($I_C = -10\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-40	-	-	Vdc
Collector – Base Breakdown Voltage ($I_C = -0.1\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	-40	-	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -0.1\text{ mA}$, $I_C = 0$)	$V_{(BR)EBO}$	-7.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = -40\text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	-	-0.1	μA dc
Emitter Cutoff Current ($V_{EB} = -7.0\text{ Vdc}$)	I_{EBO}	-	-	-0.1	μA dc

ON CHARACTERISTICS

DC Current Gain (Note 4) ($I_C = -10\text{ mA}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -500\text{ mA}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -1.0\text{ A}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -2.0\text{ A}$, $V_{CE} = -2.0\text{ V}$)	h_{FE}	150 150 150 150	- - - -	- - - -	
Collector – Emitter Saturation Voltage (Note 4) ($I_C = -0.1\text{ A}$, $I_B = -0.010\text{ A}$) (Note 5) ($I_C = -1.0\text{ A}$, $I_B = -0.100\text{ A}$) ($I_C = -1.0\text{ A}$, $I_B = -0.010\text{ A}$) ($I_C = -2.0\text{ A}$, $I_B = -0.020\text{ A}$)	$V_{CE(sat)}$	- - - -	- -0.100 - -	-0.020 -0.120 -0.200 -0.300	V
Base – Emitter Saturation Voltage (Note 4) ($I_C = -1.0\text{ A}$, $I_B = -0.01\text{ A}$)	$V_{BE(sat)}$	-	-0.76	-0.900	V
Base – Emitter Turn-on Voltage (Note 4) ($I_C = -2.0\text{ A}$, $V_{CE} = -3.0\text{ V}$)	$V_{BE(on)}$	-	-0.80	-0.900	V
Cutoff Frequency ($I_C = -100\text{ mA}$, $V_{CE} = -5.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	140	-	-	MHz
Input Capacitance ($V_{EB} = -0.5\text{ V}$, $f = 1.0\text{ MHz}$)	C_{ibo}	-		500	pF
Output Capacitance ($V_{CB} = -3.0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	-		100	pF

SWITCHING CHARACTERISTICS

Delay ($V_{CC} = 30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_d	-	-	70	ns
Rise ($V_{CC} = 30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_r	-	-	150	ns
Storage ($V_{CC} = 30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_s	-	-	525	ns
Fall ($V_{CC} = 30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_f	-	-	155	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 μsec , Duty Cycle $\leq 2\%$.
5. Guaranteed by design but not tested.

TYPICAL CHARACTERISTICS

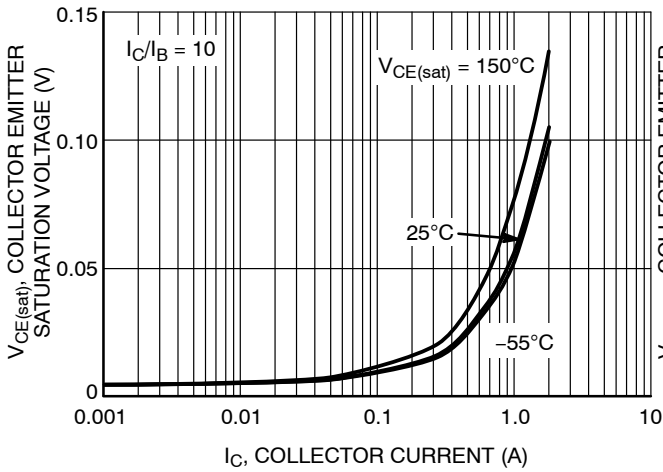


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

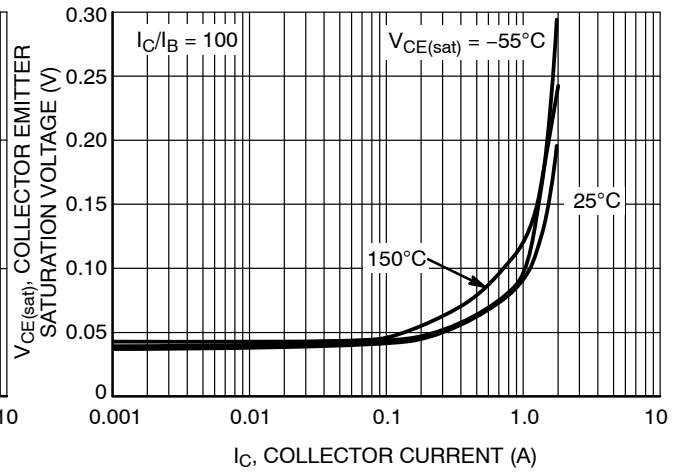


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

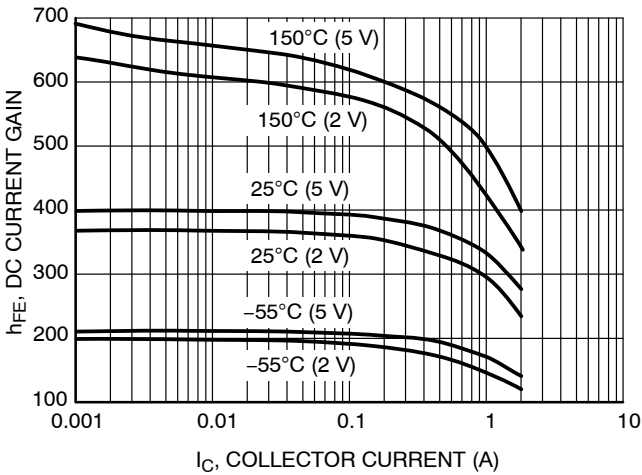


Figure 3. DC Current Gain vs. Collector Current

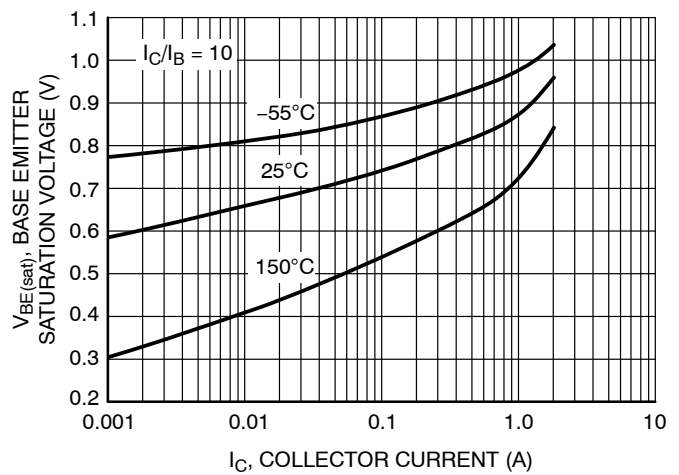


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

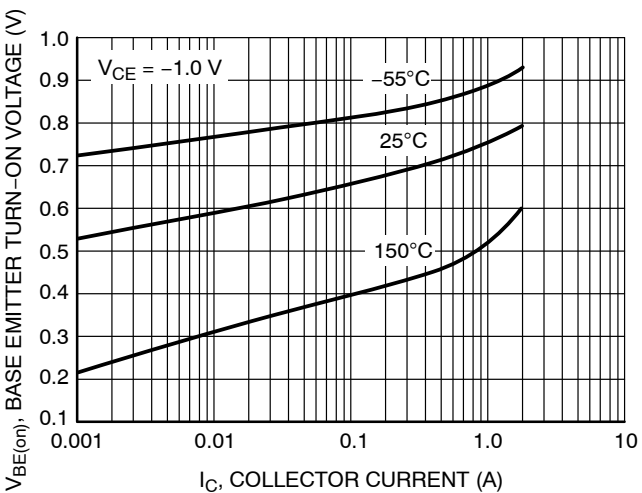


Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

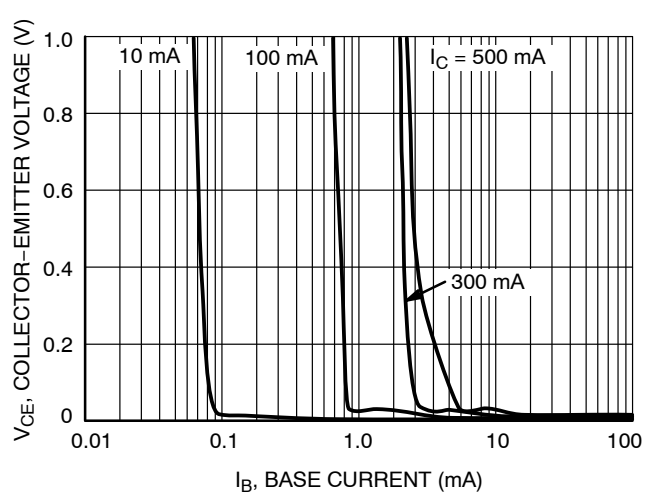


Figure 6. Saturation Region

NSS40200UW6T1G, NSV40200UW6T1G

TYPICAL CHARACTERISTICS

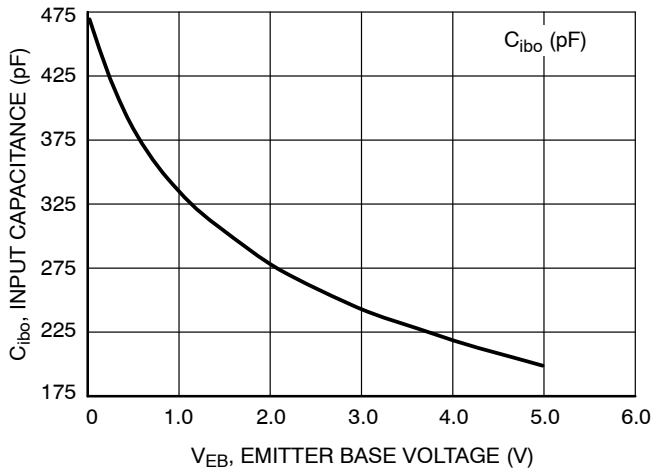


Figure 7. Input Capacitance

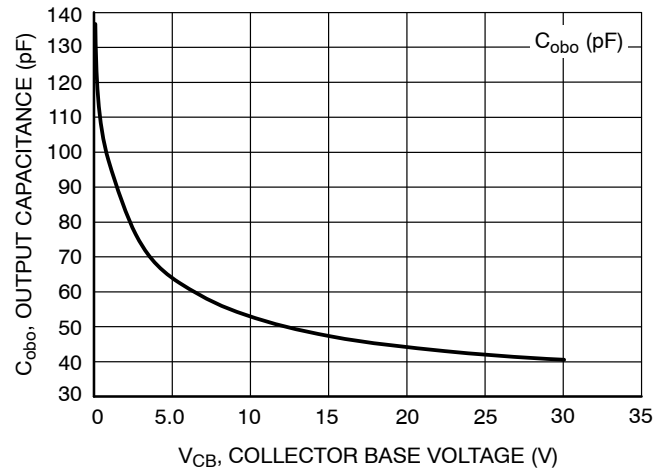


Figure 8. Output Capacitance

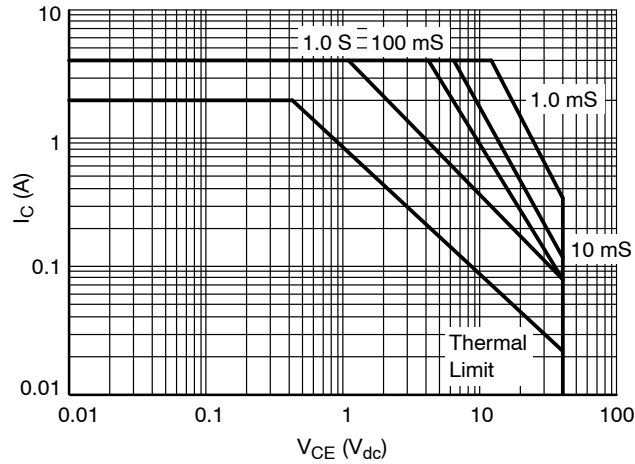


Figure 9. PNP Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



WDFN6 2x2

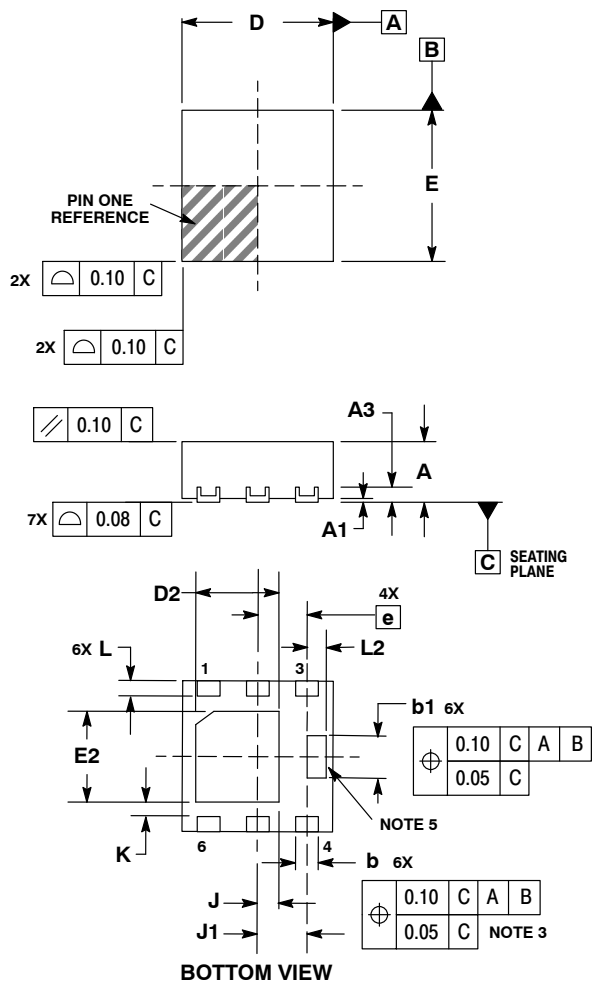
CASE 506AP-01

ISSUE B

DATE 26 APR 2006



SCALE 4:1



STYLE 1:
 PIN 1. DRAIN
 2. DRAIN
 3. GATE
 4. SOURCE
 5. DRAIN
 6. DRAIN

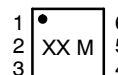
STYLE 2:
 PIN 1. COLLECTOR
 2. COLLECTOR
 3. BASE
 4. EMITTER
 5. COLLECTOR
 6. COLLECTOR

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
1. CENTER TERMINAL LEAD IS OPTIONAL. TERMINAL LEAD IS CONNECTED TO TERMINAL LEAD # 4.
2. PINS 1, 2, 5 AND 6 ARE TIED TO THE FLAG.

DIM	MILLIMETERS	
	MIN	MAX
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
b	0.25	0.35
b1	0.51	0.61
D	2.00 BSC	
D2	1.00	1.20
E	2.00 BSC	
E2	1.10	1.30
e	0.65 BSC	
K	0.15 REF	
L	0.20	0.30
L2	0.20	0.30
J	0.27 REF	
J1	0.65 REF	

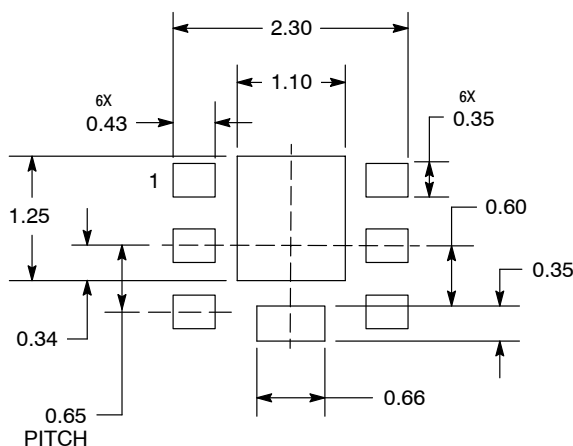
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
 M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

SOLDERMASK DEFINED MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98AON20860D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	6 PIN WDFN 2X2, 0.65P	PAGE 1 OF 1

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